

**Application Data Sheet****Application Information**

Application number::	Not Yet Assigned
Application Type::	Utility
Subject Matter::	Utility
Suggested Group Art Unit::	N/A
CD-ROM or CD-R?::	No
Sequence submission?::	No
Computer Readable Form (CRF)?::	No
Title::	Method of Forming a Barrier Metal in a Semiconductor Device
Attorney Docket Number::	29936/39479
Request for Early Publication?::	No
Request for Non-Publication?::	No
Small Entity?::	No
Petition included?::	No
Secrecy Order in Parent Appl.?::	No

**Applicant Information**

Applicant Authority Type::	Inventor
Primary Citizenship Country::	
Status::	
Given Name::	Chang Jin
Family Name::	KO
City of Residence::	
Country of Residence::	Republic of Korea
Street of mailing address::	San 136-1, Ami-Ri, Bubal-Uep, Ichon-Shi, Kyungki-Do
City of mailing address::	
Country of mailing address::	Republic of Korea
Postal or Zip Code of mailing address::	

**Correspondence Information**

Correspondence Customer Number:: 04743  
Phone number:: (312) 474-6300  
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**Representative Information**

Representative Customer Number:: 04743

**Domestic Priority Information**

Application:: Continuity Type:: Parent Application:: Parent Filing Date::  
This Application

**Foreign Priority Information**

Country::	Application number::	FilingDate::	Priority Claimed::
Republic of Korea	10-2002-0084338	December 26, 2002	

**Assignee Information**

Assignee name:: Hynix Semiconductor Inc., of San 136-1,  
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